GaSb/GaAs quantum dots: staggered type-II band alignment
- large confinement of holes (up to 450 meV)
- electrons weakly confined within host material
- low recombination energy, long exciton lifetime
- possible application within IR-lasers and optical storage devices

GaSb/GaAs nanostructures: Quantum wells, dots, and rings
- Growth, atomic structure, and type-II band alignment of GaSb/GaAs nanostructures: Quantum wells, dots, and rings
- Quantum rings especially interesting for charge storage
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